



Potential performance of N-doping and Nb_3Sn for FCC

Sam Posen

FCC Week

30 May 2017



Fermilab/CERN Collaboration



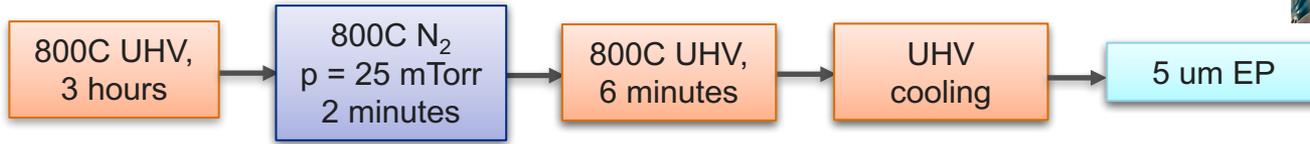
- Study N-doping and Nb₃Sn in frequency range appropriate for FCC
- New high Q₀ technologies were harnessed to reduce cryopower requirements for LCLS-II

	FCC-ee ttbar	LCLS-II
# of cavities	>650	384
Duty factor	100%	100%
RF voltage	11 GeV	4 GeV

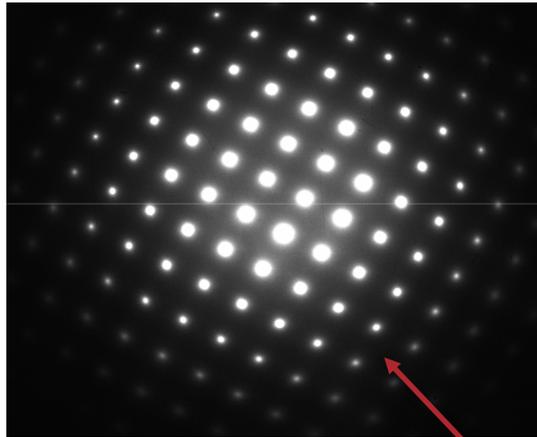
- Nb₃Sn cavities are under study and show great promise for high Q₀ operation at 4.4 K
- What are the potential of these technologies for FCC?

1. Nitrogen Doping and Minimizing Trapped Flux Losses

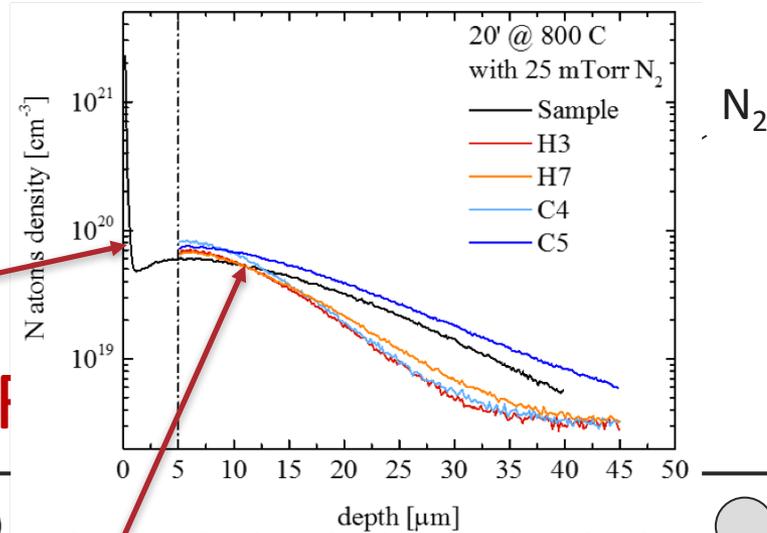
N-doping treatment – “2/6” recipe



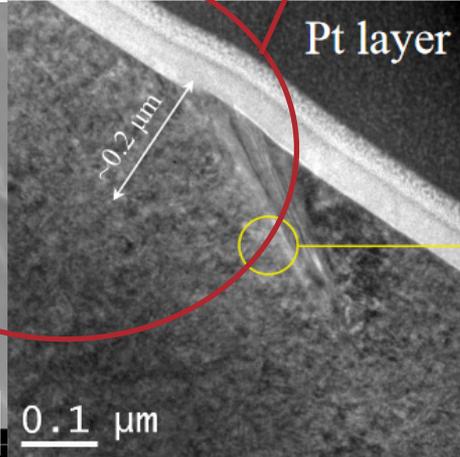
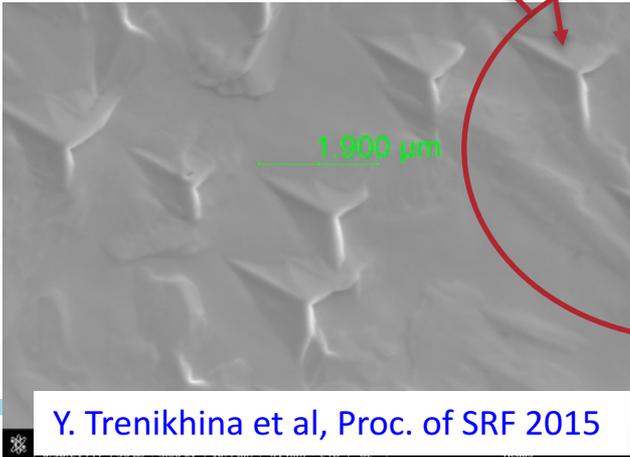
Y. Trenikhina et Al, Proc. of SRF 2015



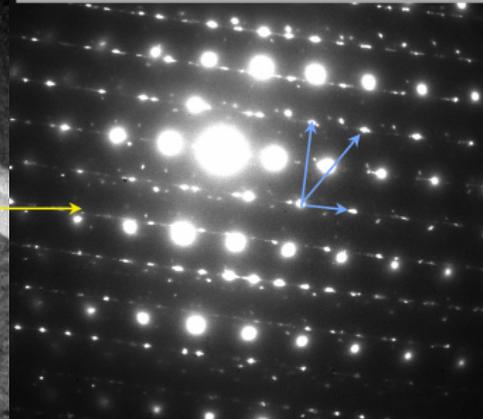
Final RF



Nb_xN_y
N Interstitial

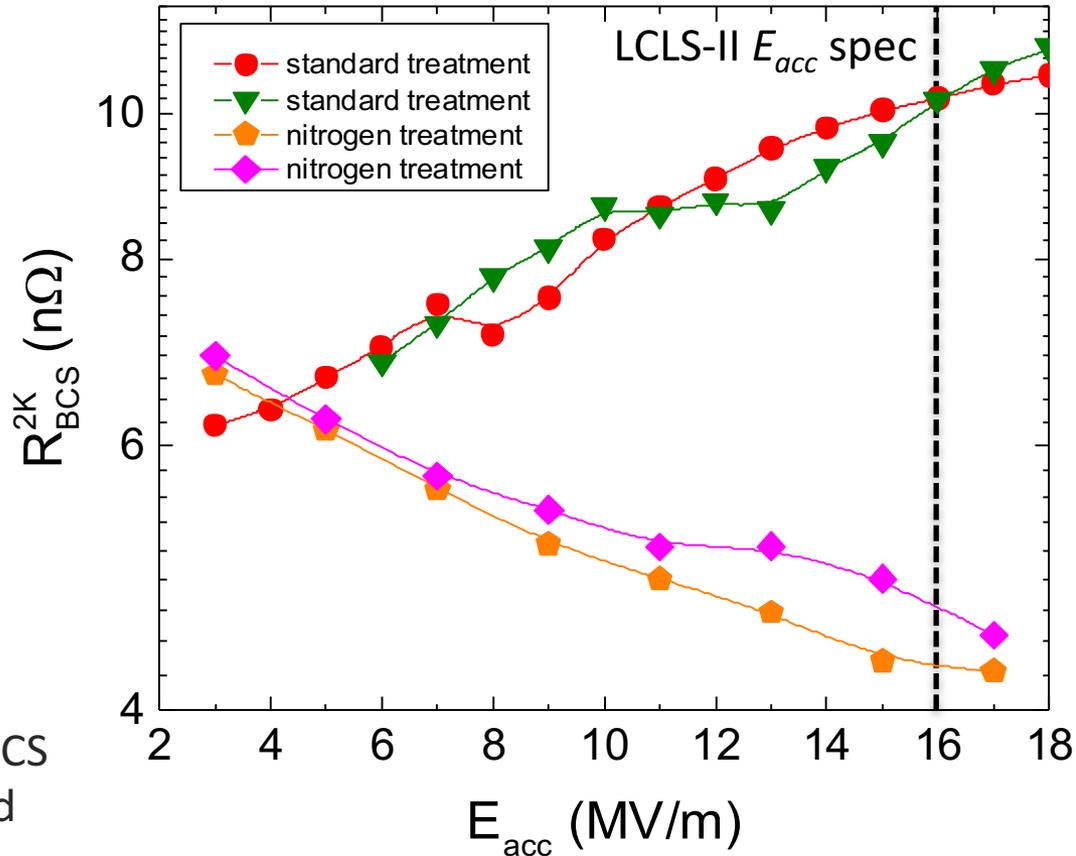
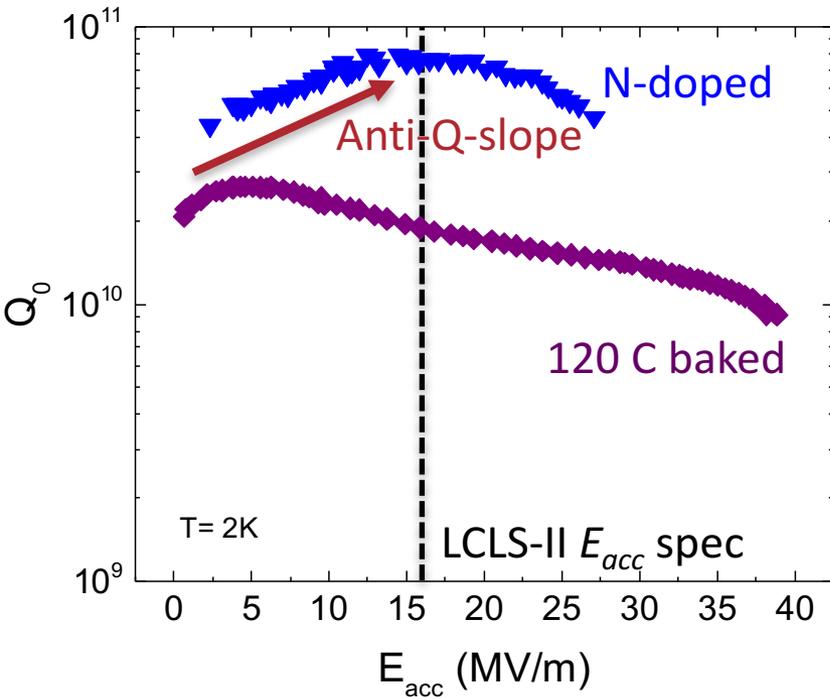


Nb [113]+Nb₂N [210]+?



Fermilab

Reduction in BCS Resistance



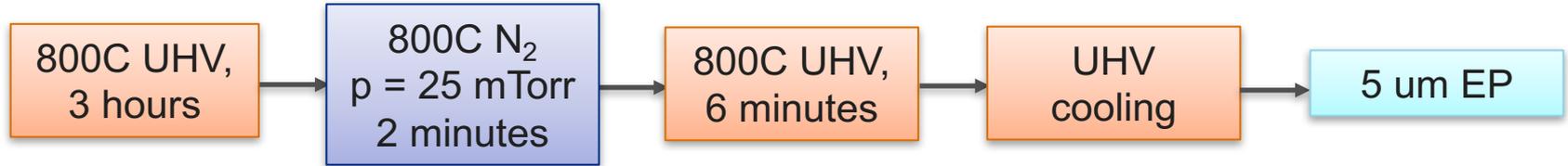
Anti-Q-slope emerges from the BCS surface resistance decreasing with field

- $>2x$ R_{BCS} improvement at 2 K, 16 MV/m
- Reduced quench field for “2/6” recipe, but generally >20 MV/m

“Doping” and “Infusion”



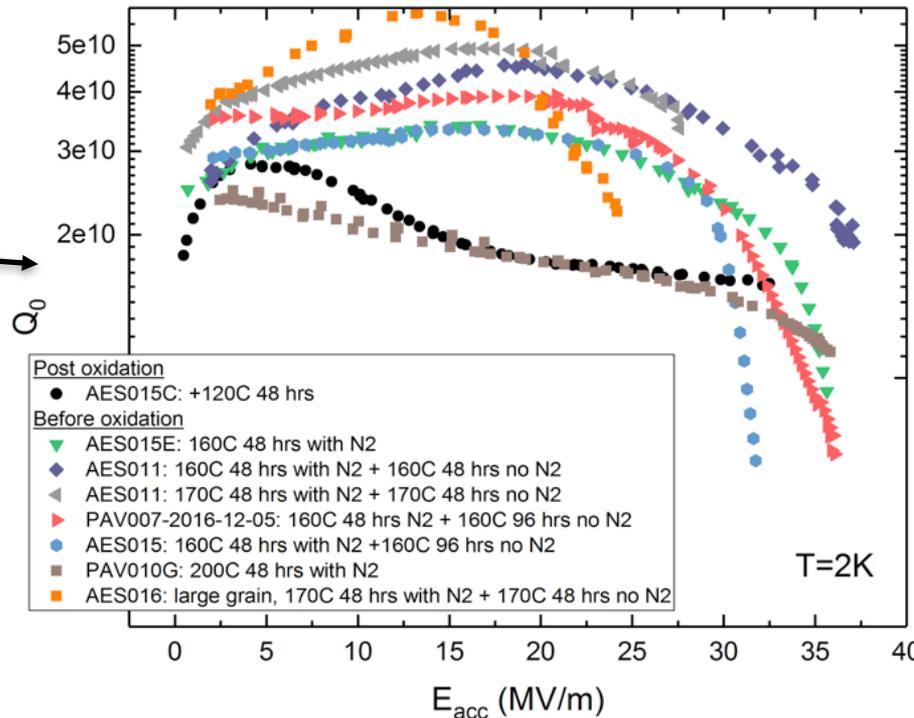
“2/6” Nitrogen “Doping”



120 C Nitrogen “Infusion”



Can tailor treatment to application (optimize for Q_0 at a given E_{acc})

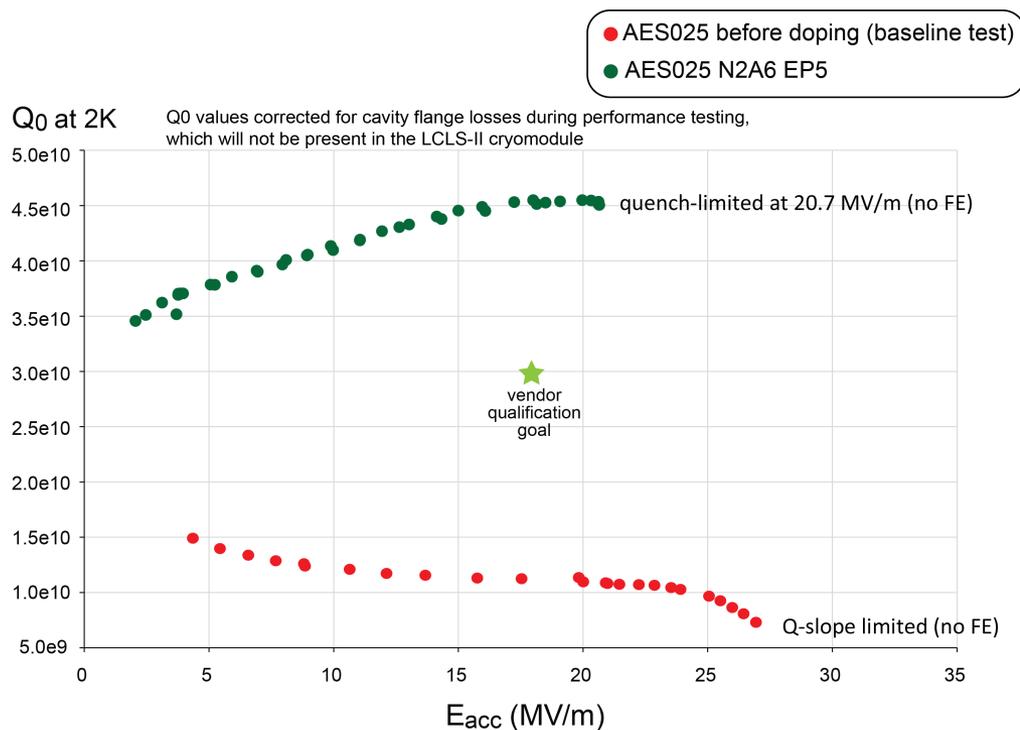


A. Grassellino et al.
arXiv:1701.06077

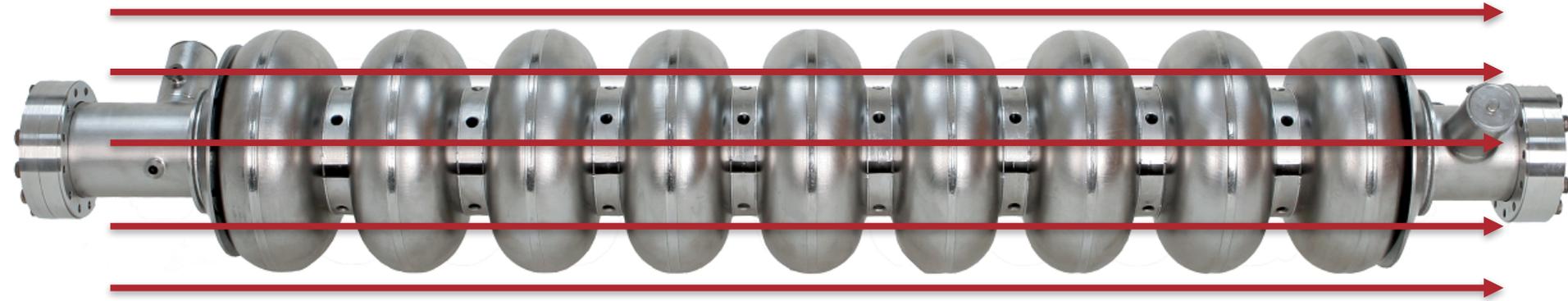


Mature Technology – Transferred to Industry

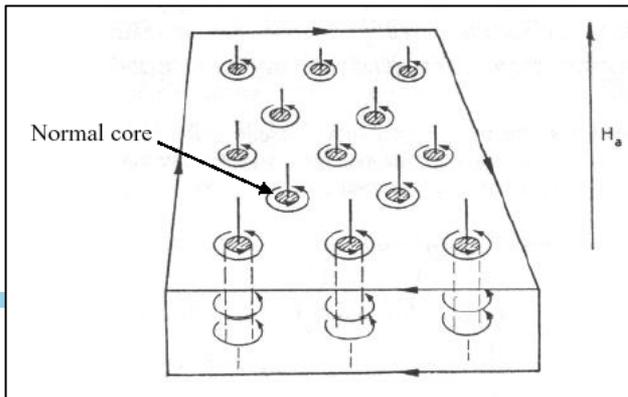
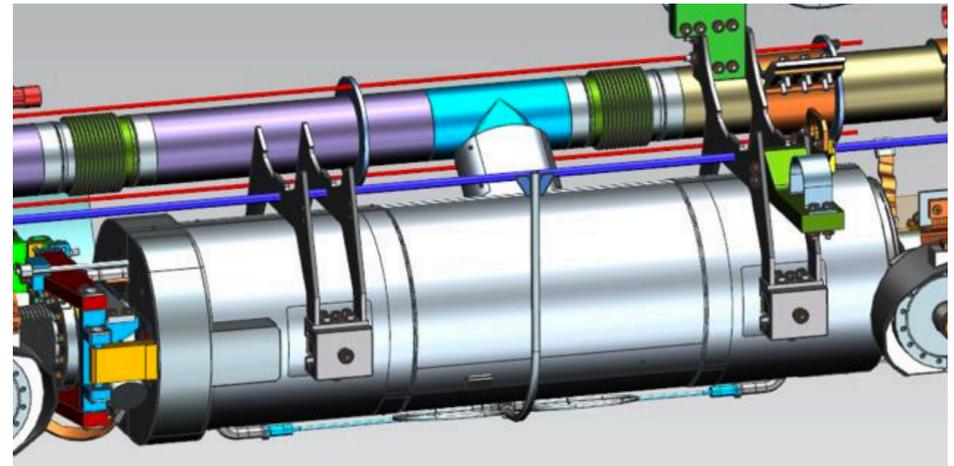
- SRF cavity vendors: from niobium material to N-doped cavities ready for qualification testing



Effect of Trapped Magnetic Flux on Residual Resistance

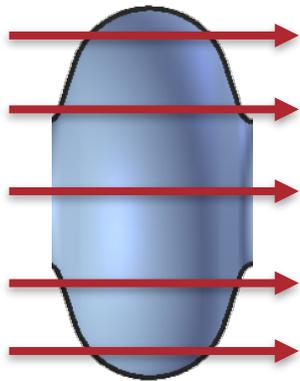
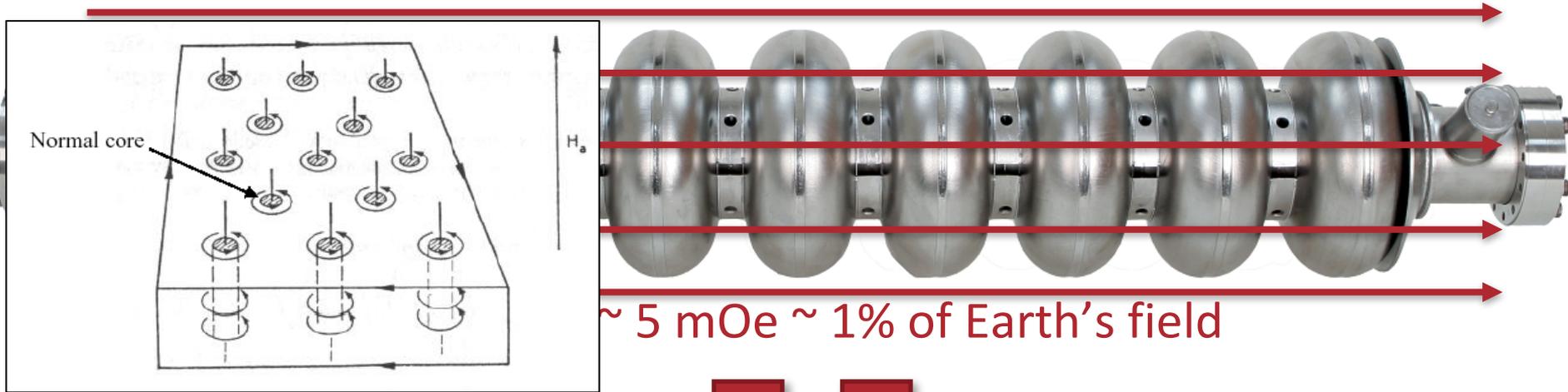


- Sensitivity to trapped flux
 - 120 C ~ 0.3 n Ω /mG
 - N-doping ~ 1.0 n Ω /mG
- Minimizing trapped flux is crucial

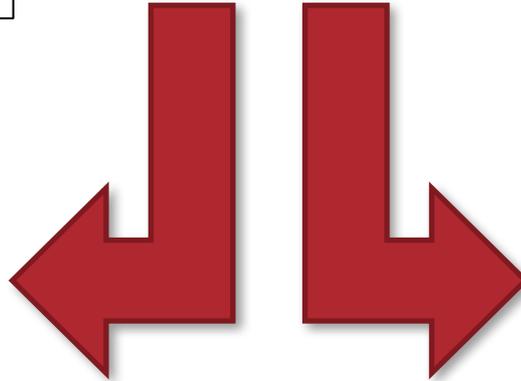


$H_{\text{shielded}} \sim 5$ mOe $\sim 1\%$ of Earth's field

Magnetic Flux Expulsion

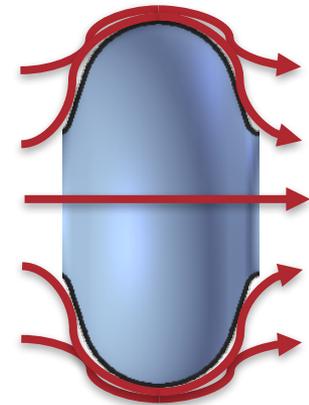


Magnetic Flux Trapping



Trapped flux increases R_{res}

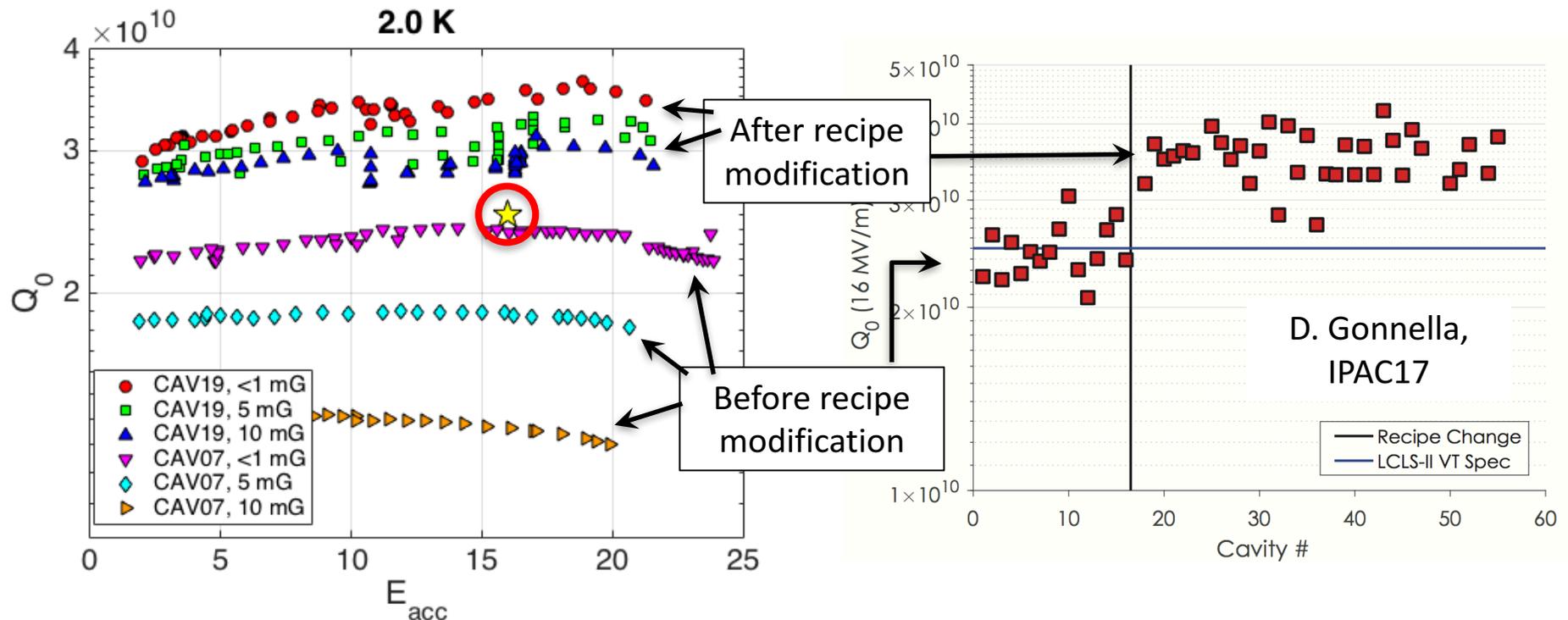
Closer to intrinsic R_{res}



Magnetic Flux Expulsion

LCLS-II – Recipe Change to Promote Expulsion

- After seeing results of first batch of 16 cavities, planned for modifications for next batch
- Modified recipe – 900 C now standard
- Significant Q_0 improvement following modification



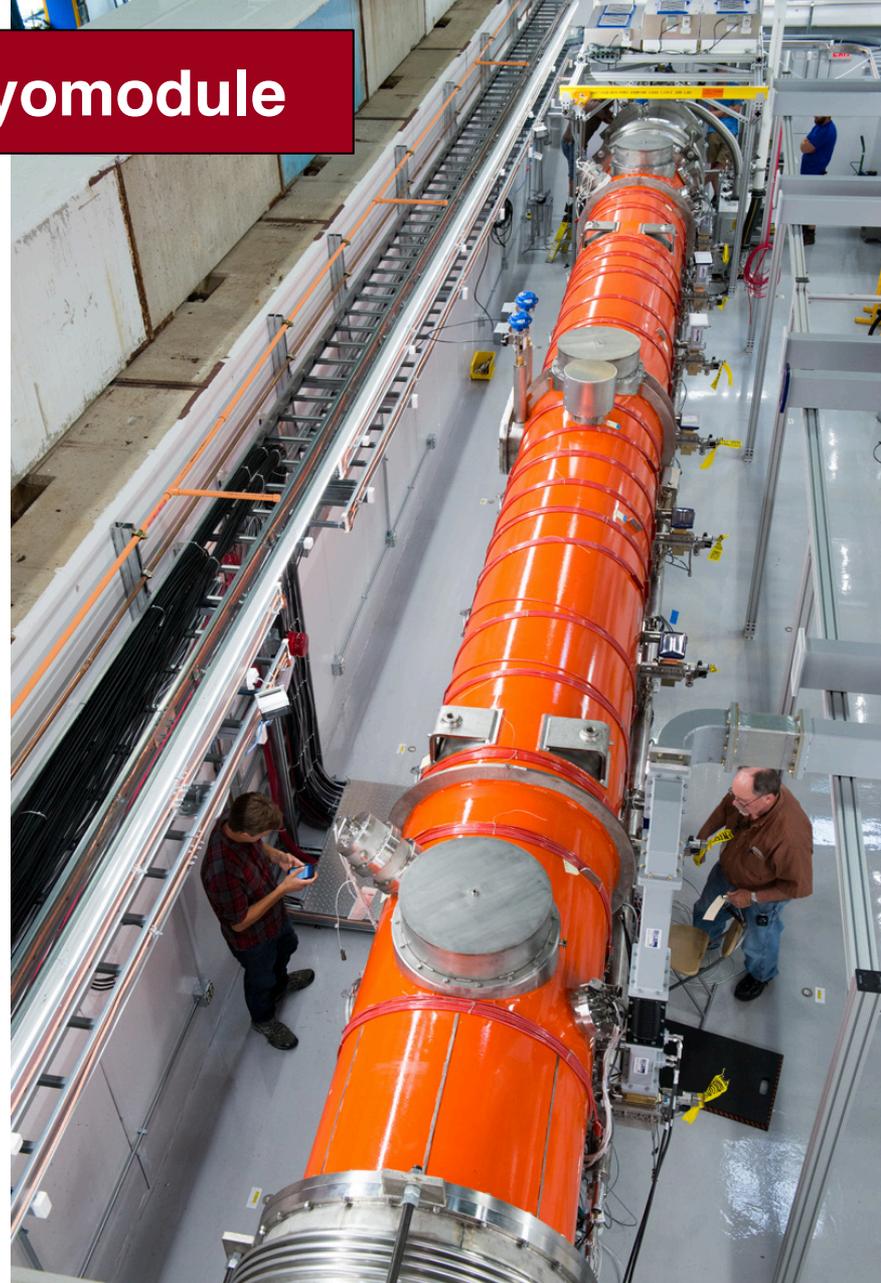
Fermilab Prototype LCLS-II Cryomodule

Cavity	Usable Gradient* [MV/m]	Q0 @16MV/m* 2K Fast Cool Down
TB9AES021	18.2	2.6E+10
TB9AES019	18.8	3.1E+10
TB9AES026	19.8	3.6E+10
TB9AES024	20.5	3.1E+10
TB9AES028	14.2	2.6E+10
TB9AES016	16.9	3.3E+10
TB9AES022	19.4	3.3E+10
TB9AES027	17.5	2.3E+10
Average	18.2	3.0E+10
Total Voltage	148.1 MV	

Spec:
133 MV



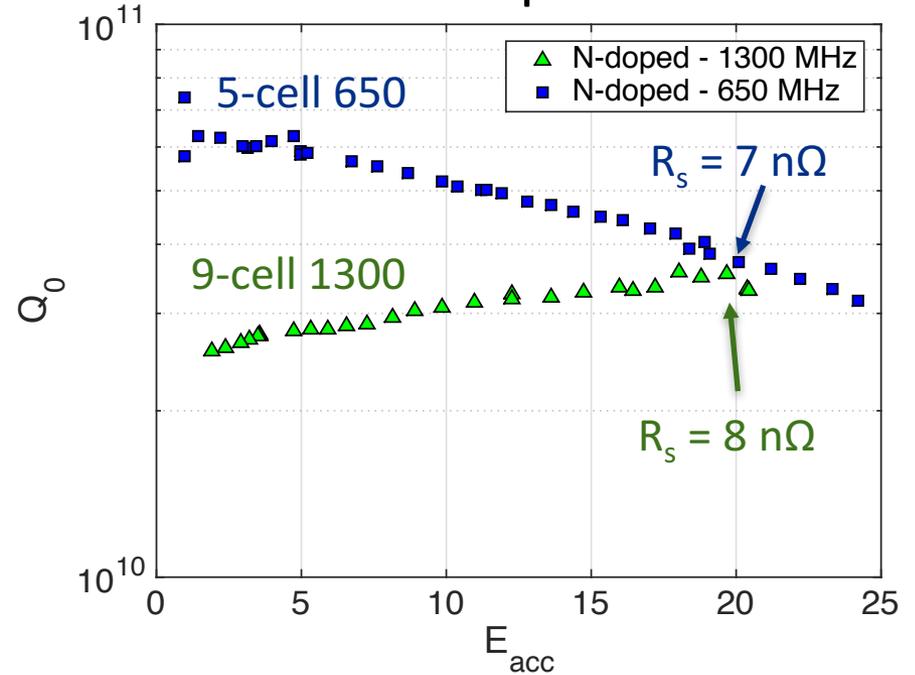
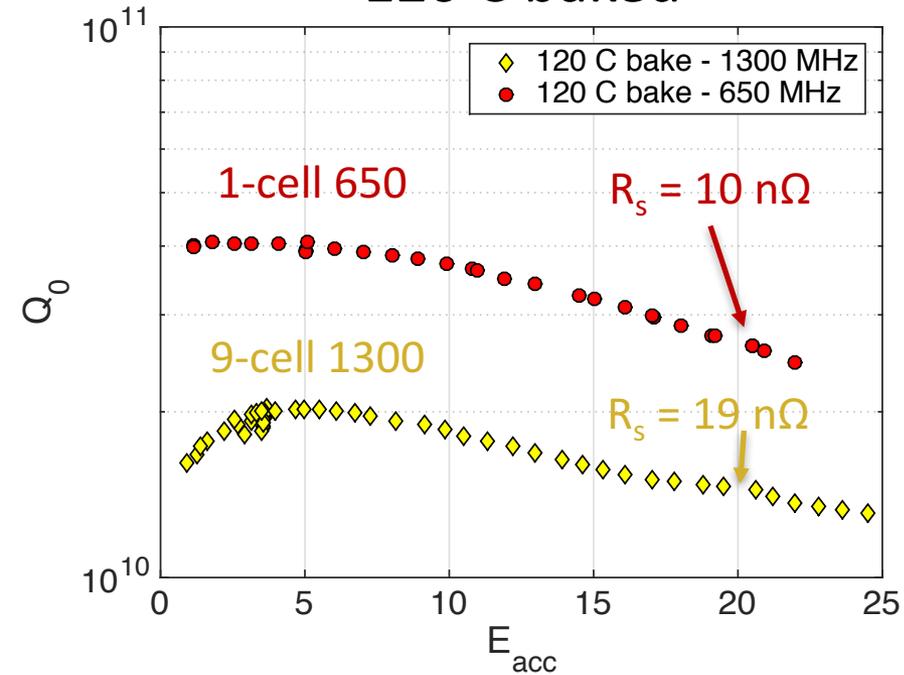
Spec:
 2.7×10^{10}



Variation with Frequency

120 C baked

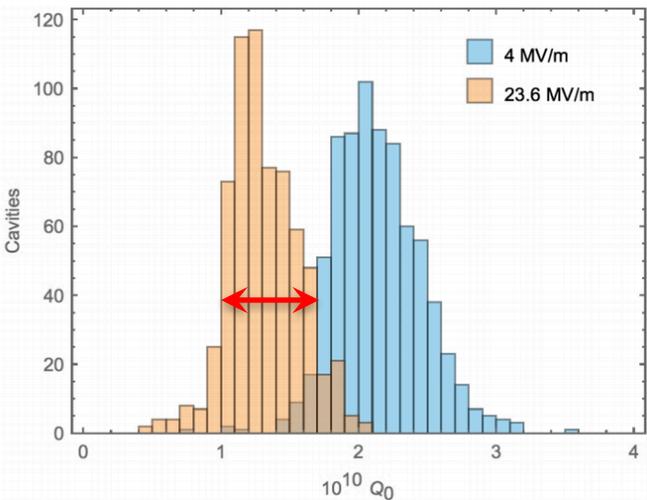
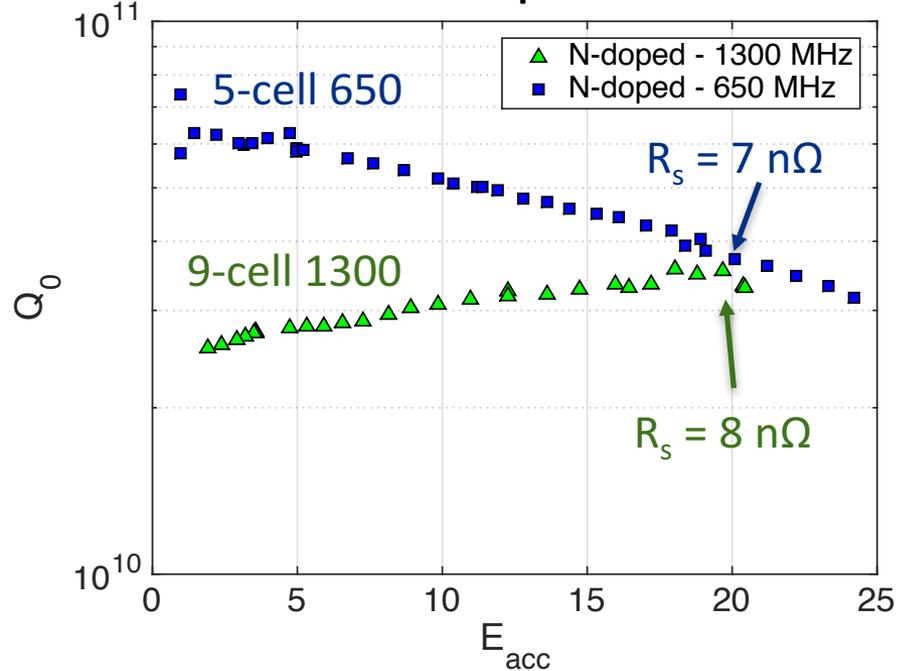
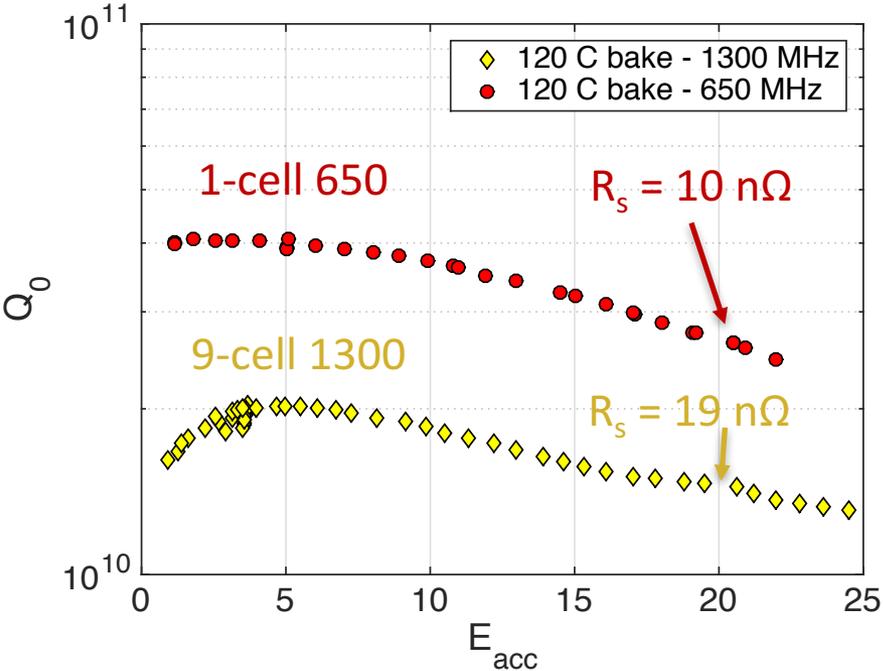
N-doped



Variation with Frequency

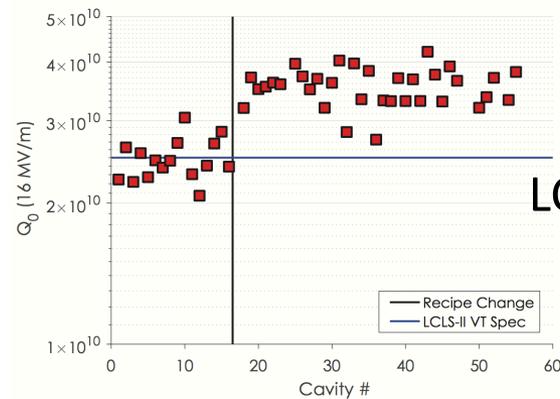
120 C baked

N-doped



XFEL: $\sim 18-27 \text{ n}\Omega$
at 23.6 MV/m

Can improve
mag. shielding,
flux expulsion

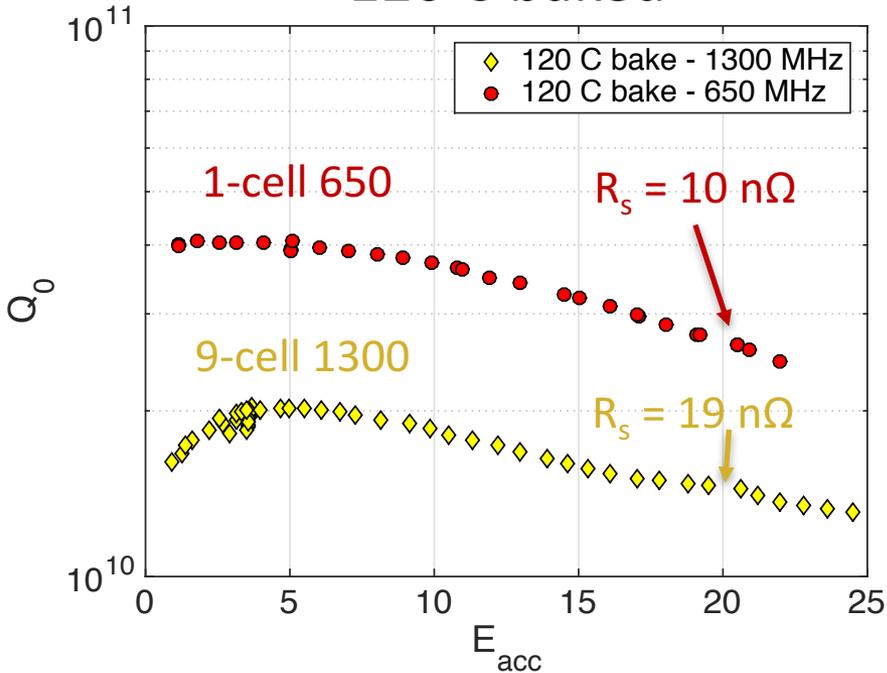


LCLS-II: $< 10 \text{ n}\Omega$
at 16 MV/m

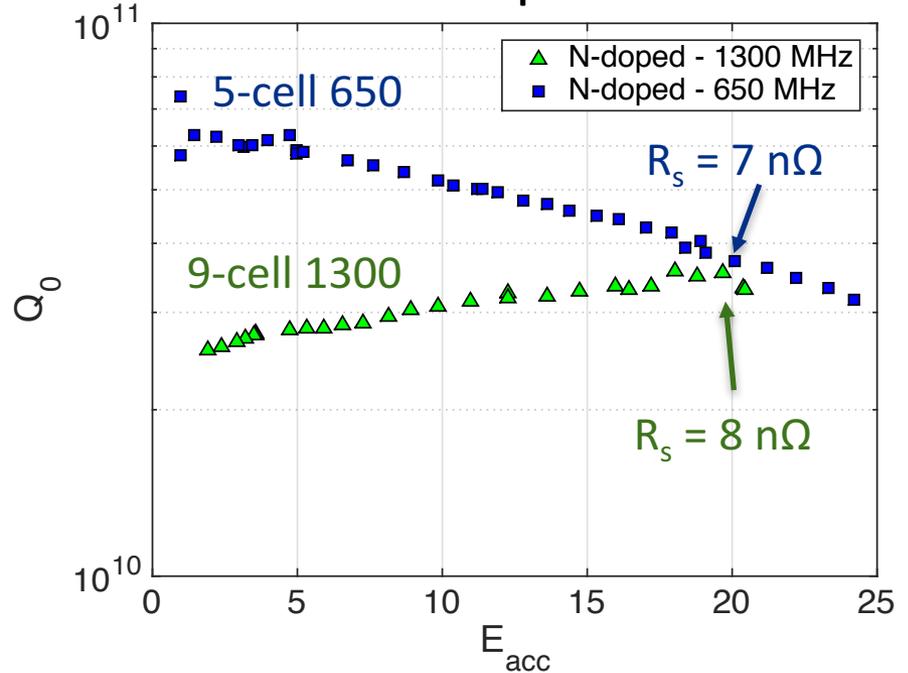


Variation with Frequency

120 C baked



N-doped



- Use decomposition to help interpolate to **800 MHz** at 20 MV/m (using expected scaling for BCS and residual resistance)
 - 120 C baked: 12 nΩ
 - N-doped: 8 nΩ

*Additional details given in appendix slides. Frequency scaling from M. Martinello et al. [to be published]

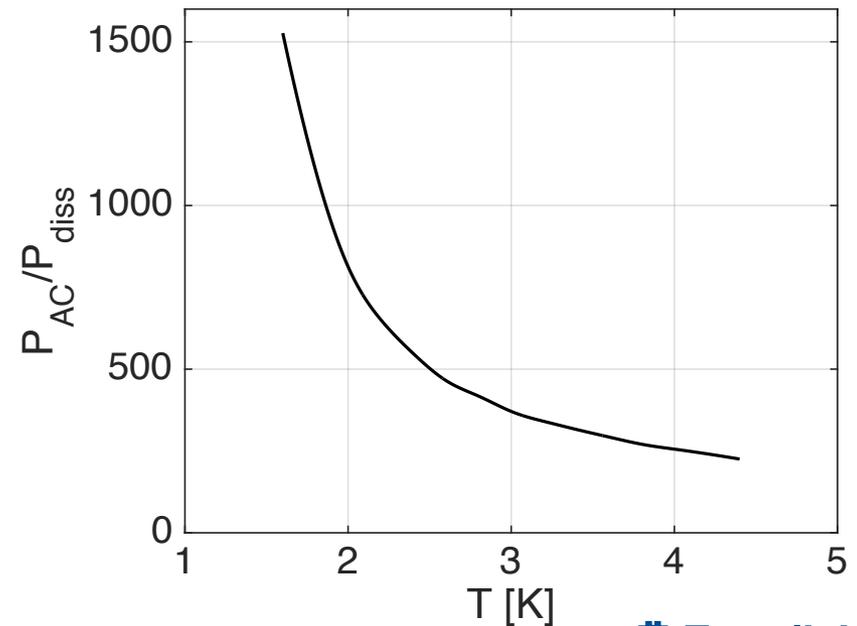
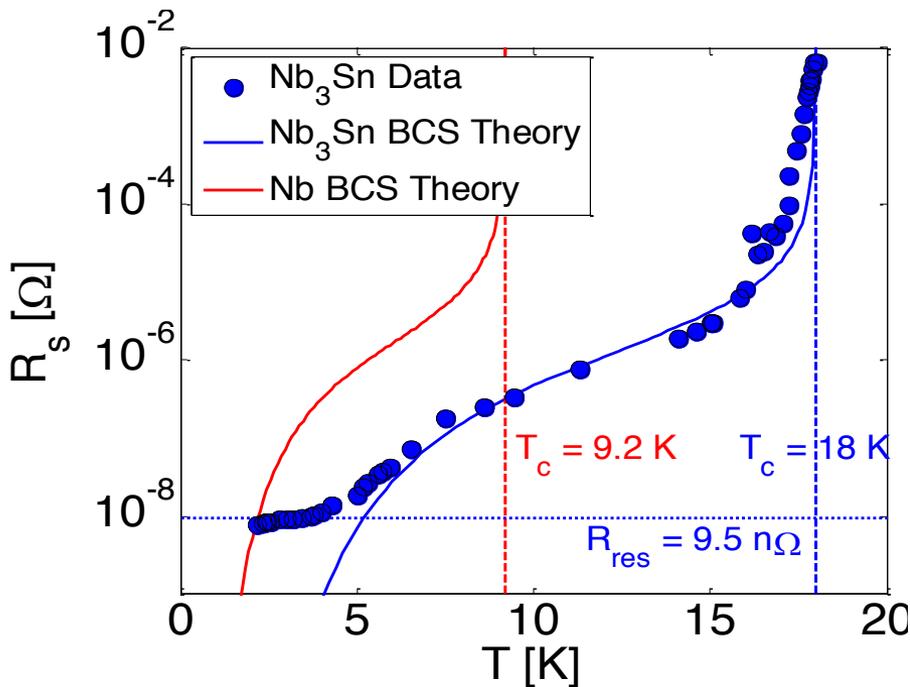
2. Nb₃Sn

Higher $Q_0(T)$ with Nb_3Sn

- Large $T_c \sim 18$ K
 - Very small $R_{BCS}(T) - R_{BCS}(T) \sim e^{-1.76T_c/T}$
 - High Q_0 even at relatively high T
- Higher temperature operation
 - Simpler cryogenic plant
 - Higher efficiency



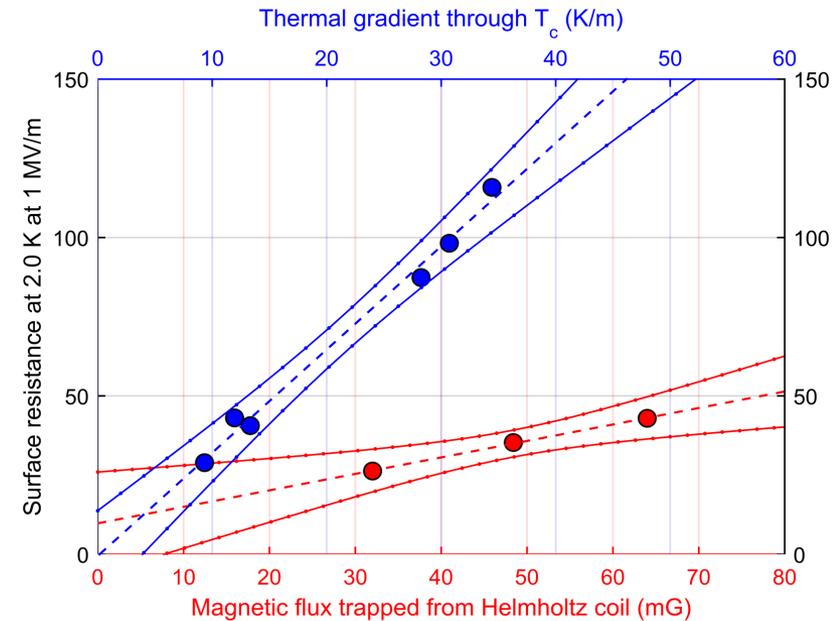
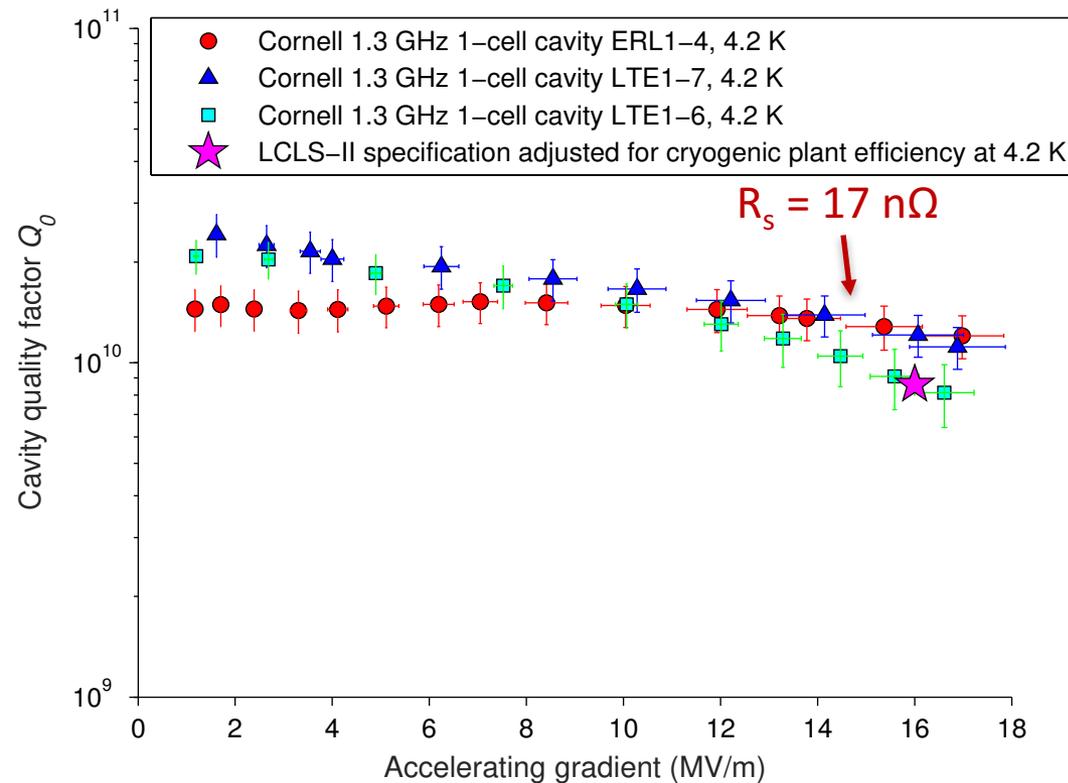
CERN cryogenic plant



State-of-the-Art



- Cornell: repeatable achievement of 14-17 MV/m with $Q \sim 10^{10}$ at 4.2 K in 1.3 GHz 1-cell cavities



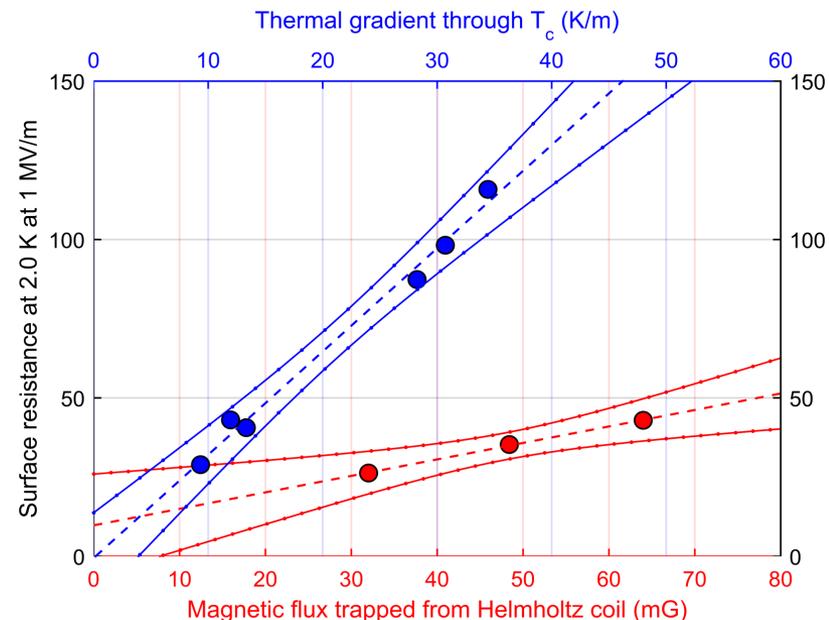
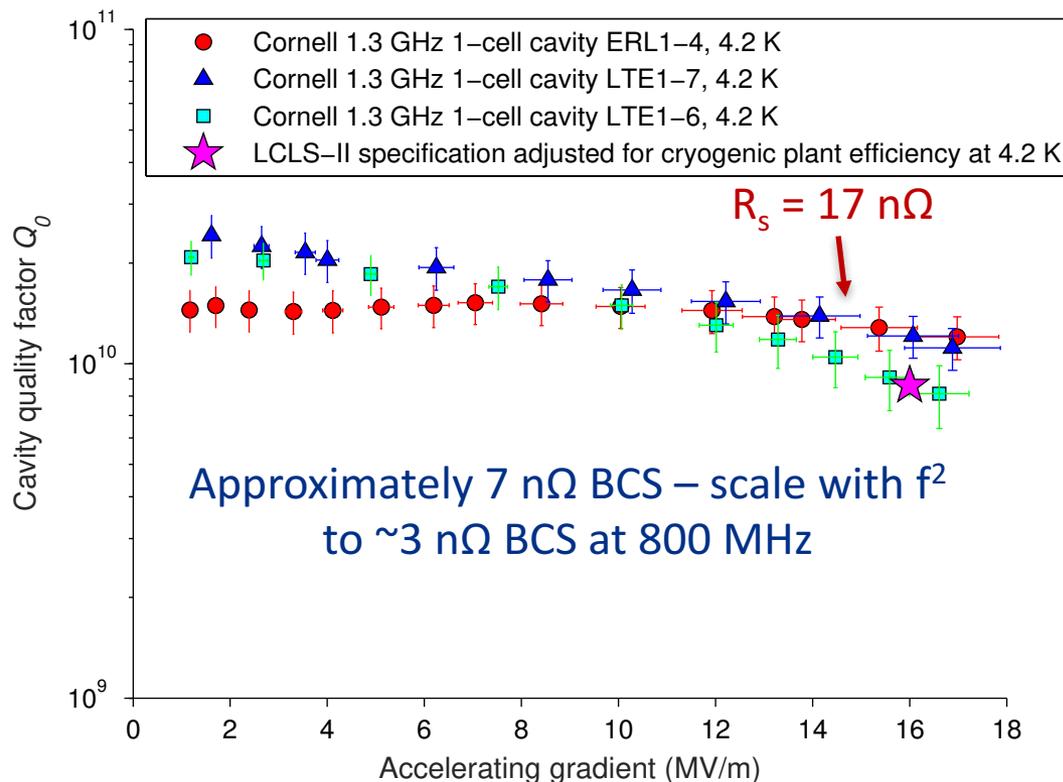
D. Hall, TTC 2017

S. Posen and D. Hall, SUST 30 033004 (2017).

State-of-the-Art



- Cornell: repeatable achievement of 14-17 MV/m with $Q \sim 10^{10}$ at 4.2 K in 1.3 GHz 1-cell cavities



D. Hall, TTC 2017

Future studies to reduce trapped flux may be able to significantly lower residual resistance

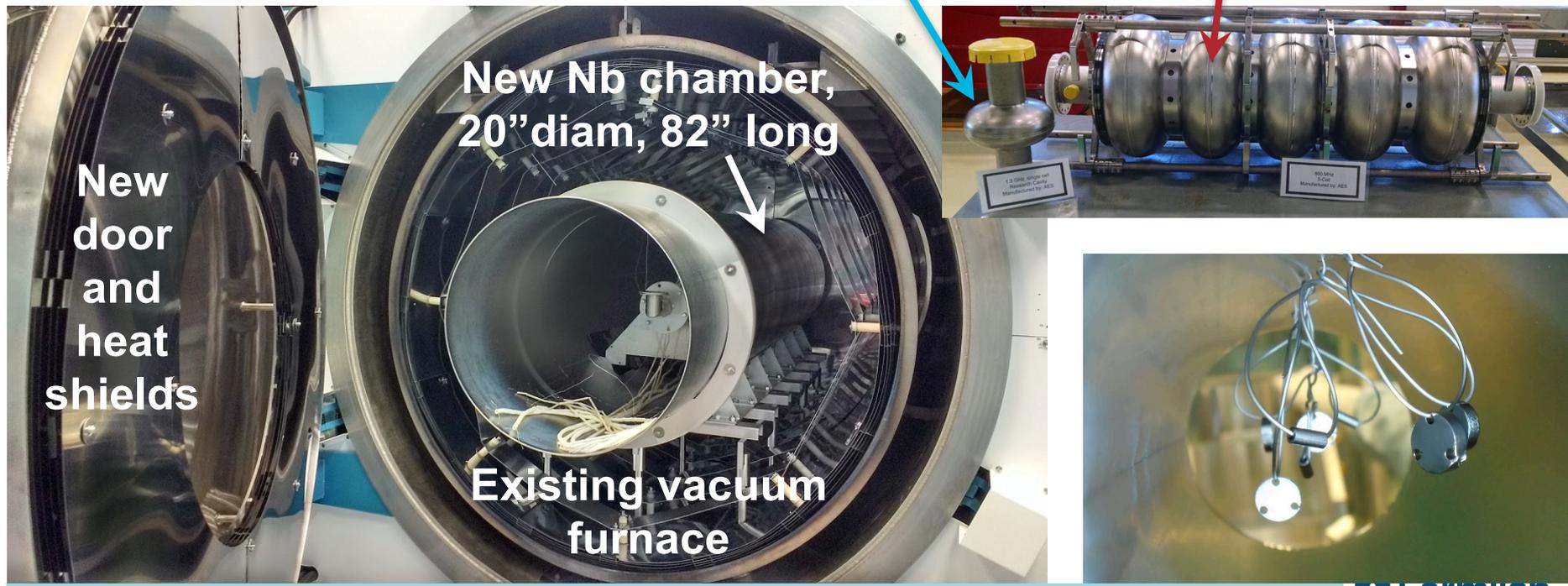
S. Posen and D. Hall, SUST 30 033004 (2017).

Scaling up to Low Frequency Multicell Cavities

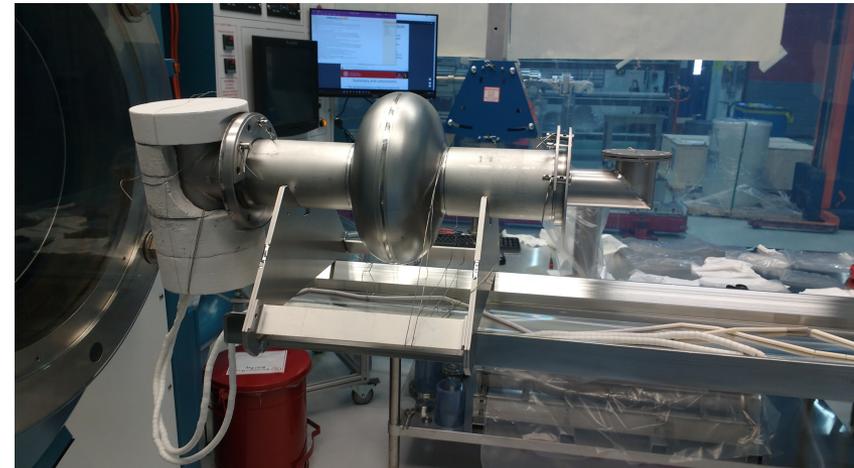
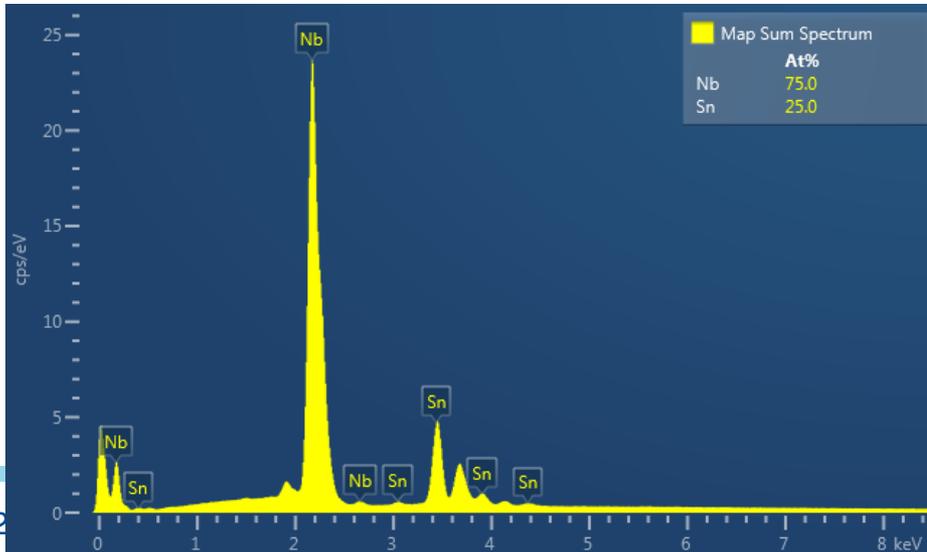
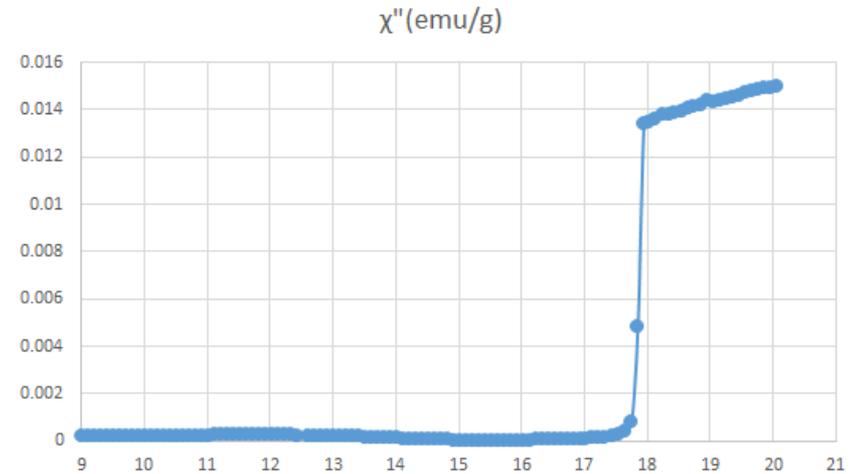
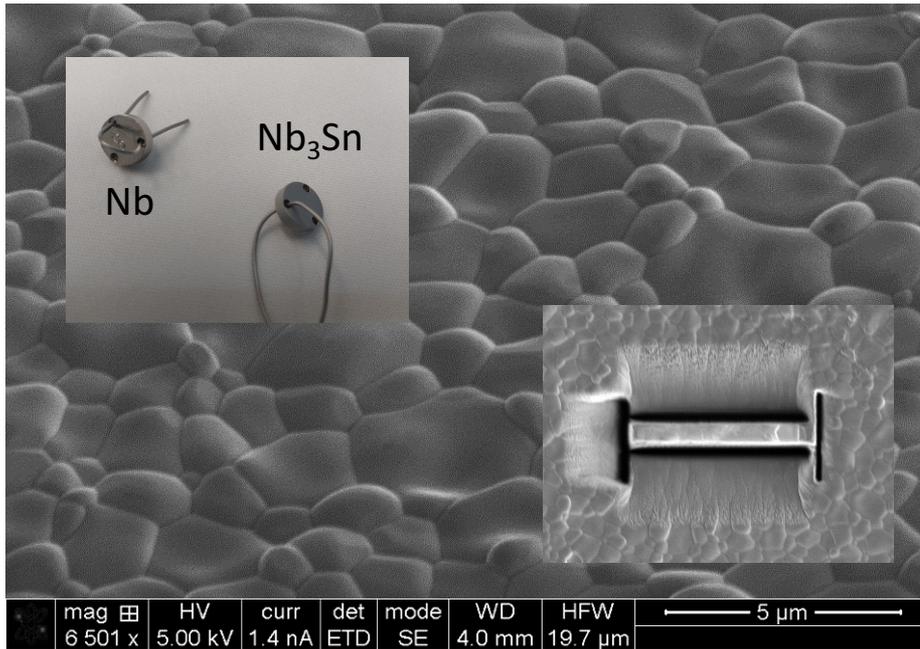
- Fermilab: large Nb₃Sn SRF coating apparatus recently commissioned
- First samples and first cavity coated in early 2017
- Collaboration with CERN to coat 800 MHz cavities

1.3 GHz 1-cell (current state of Nb₃Sn R&D)

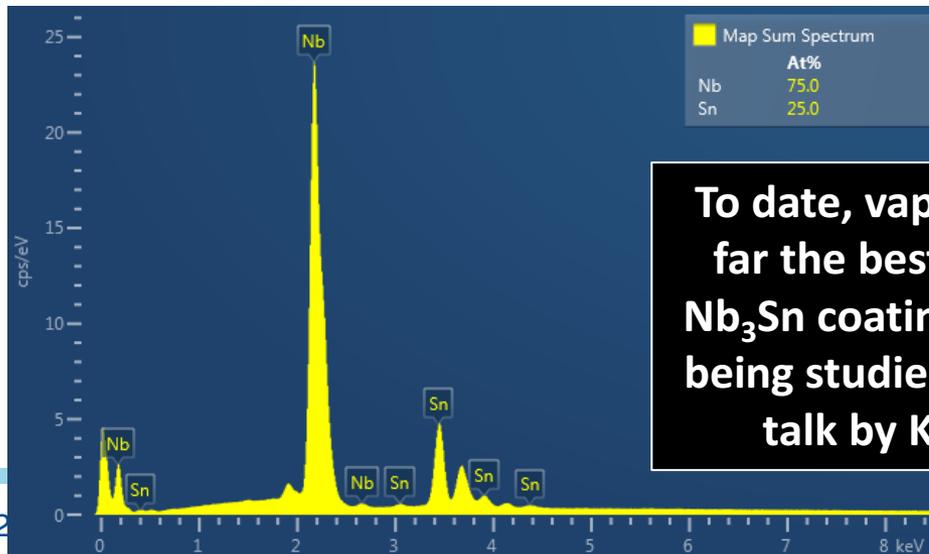
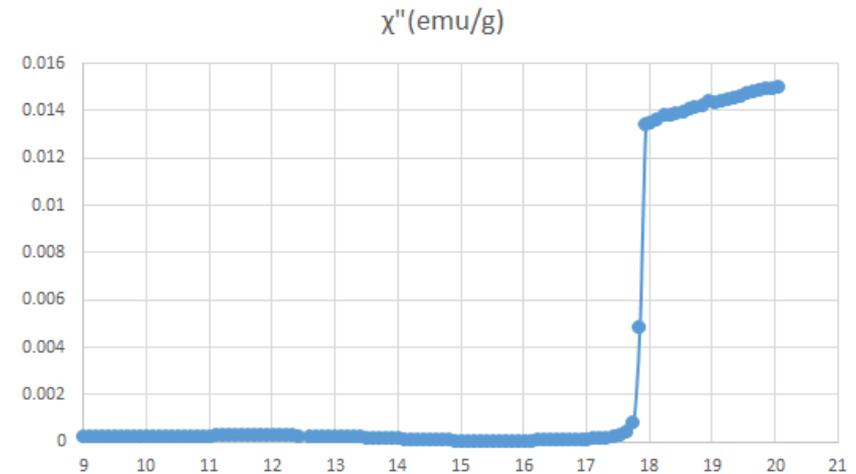
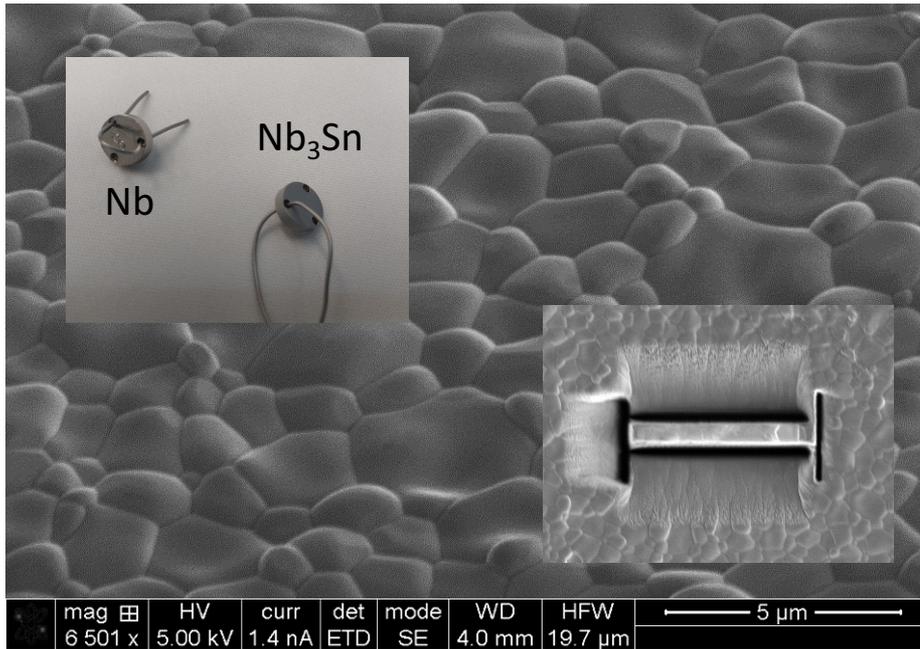
650 MHz 5-cell (future)



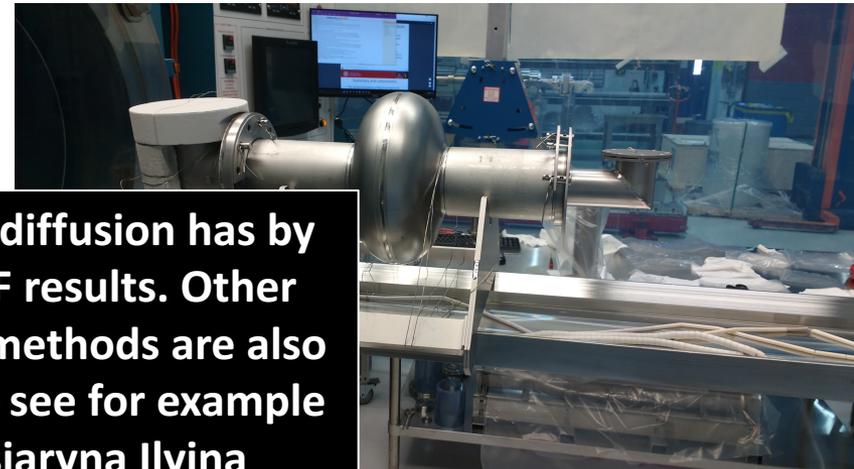
First Nb₃Sn Samples via Vapor Diffusion at FNAL



First Nb₃Sn Samples via Vapor Diffusion at FNAL

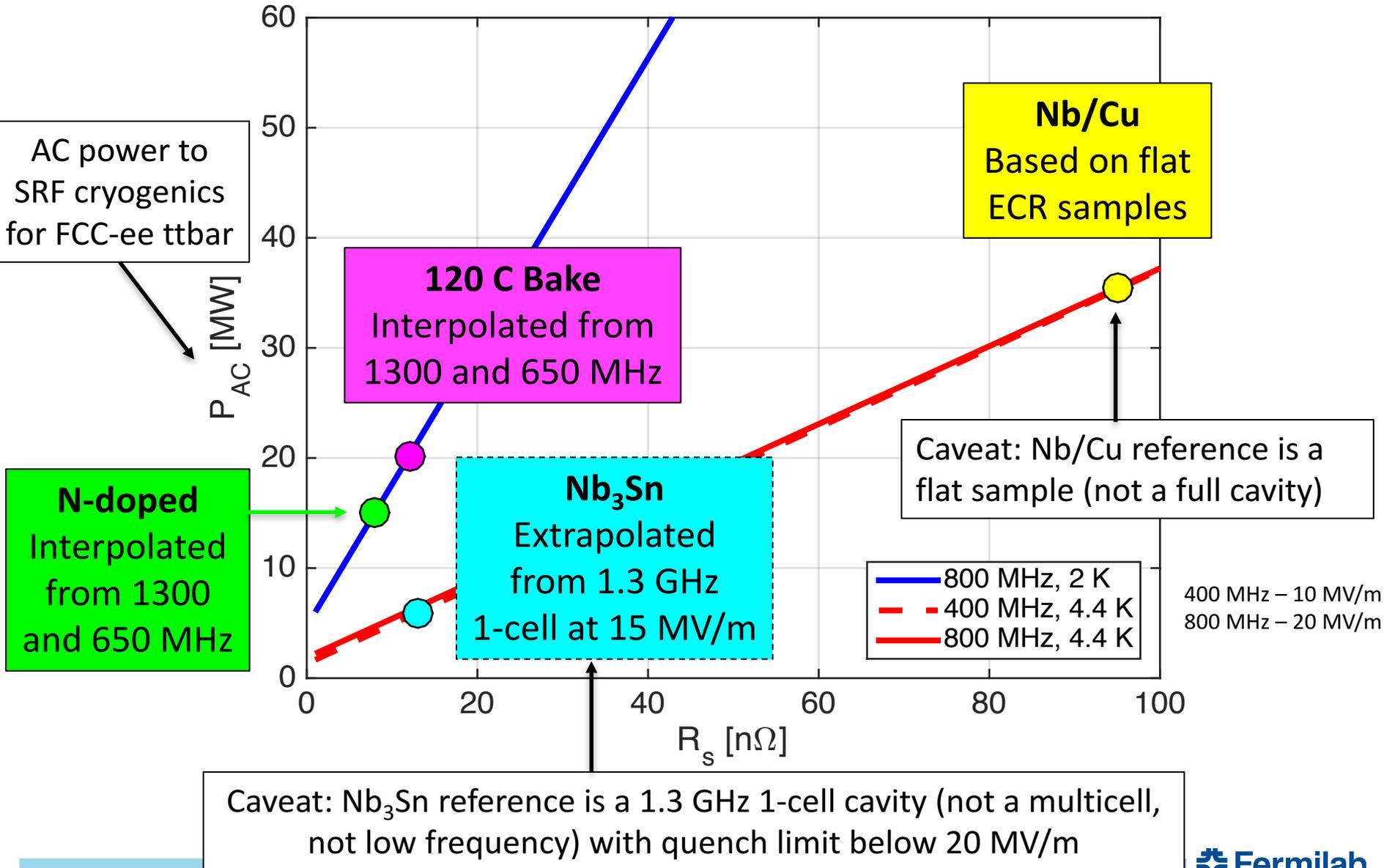


To date, vapor diffusion has by far the best RF results. Other Nb₃Sn coating methods are also being studied – see for example talk by Katsiaryna Ilyina

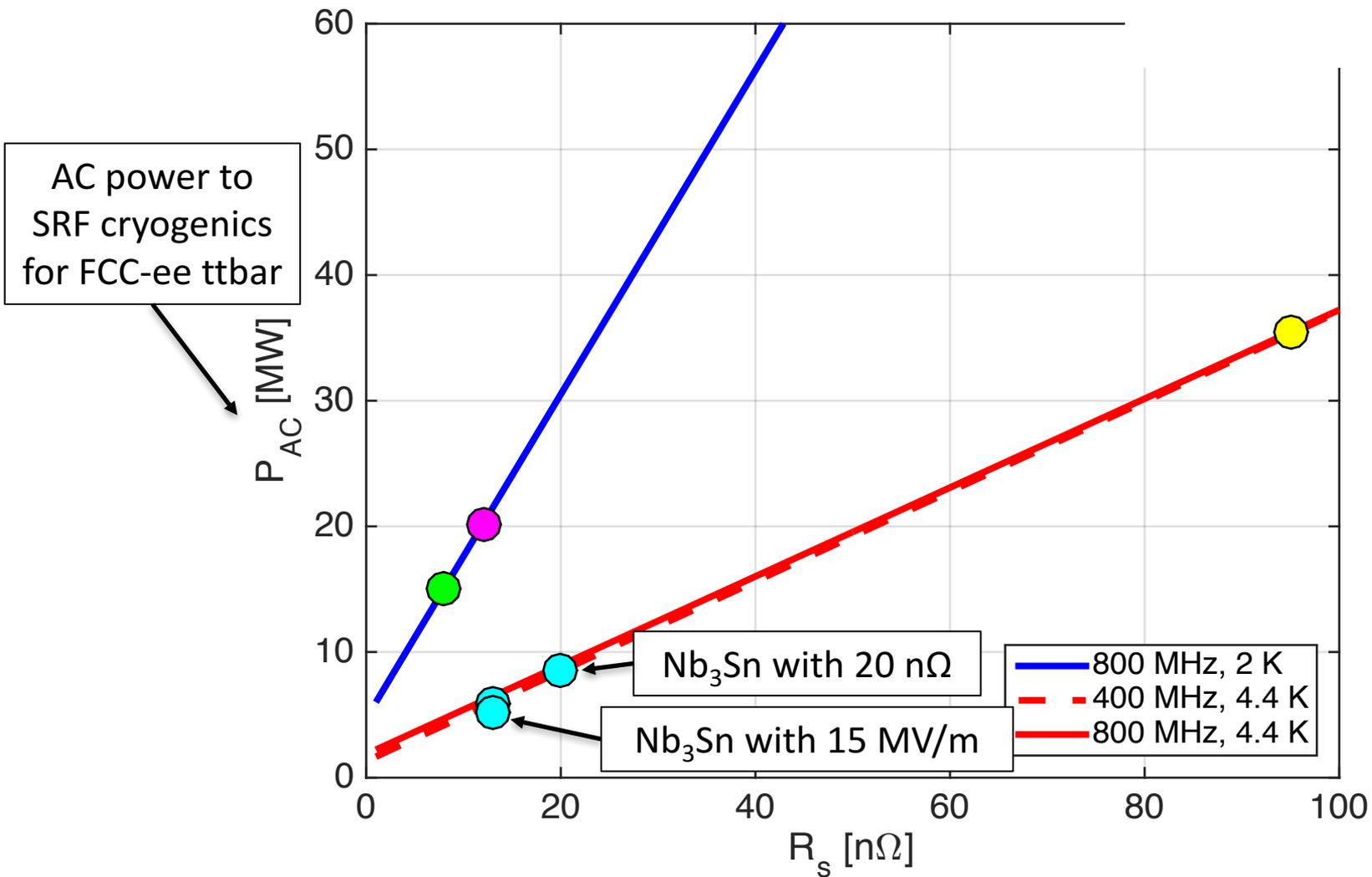


3. Predicting Potential for FCC

Potential of Different SRF Cavity Treatments



Potential of Different SRF Cavity Treatments



Summary



- Treatments applied in production to 1300 MHz cavities could be readily applied to 800 MHz cavities for FCC
- 1300 MHz and 650 MHz data were drawn on to try to estimate predicted performance at 800 MHz
- Nitrogen doping shows promise for minimizing cryopower requirements; positive results so far from LCLS-II production
- 120 C baking has relatively low cryogenic power requirements; proven in >800 cavities for XFEL (and others)
- Control of flux losses is crucial to residual resistance in all cases: magnetic 1) hygiene, 2) shielding, 3) expulsion
- Nb₃Sn promising at 4.4 K; R&D advancing for multicells & continuing to push performance

Acknowledgements



- Many thanks to Alex Melnychuk, Martina Martinello, and Anna Grassellino for contributions
- Many thanks to Sarah Aull for helping to make AC power calculations consistent with CERN

Appendix. Assumptions, Calculations, References

Assumptions



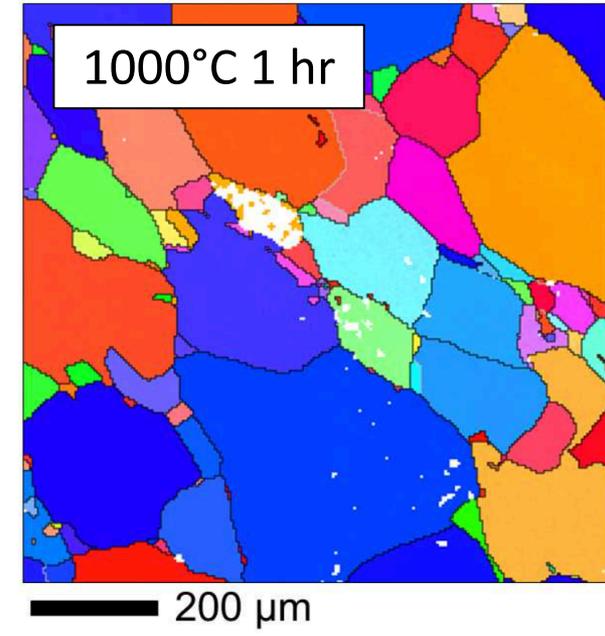
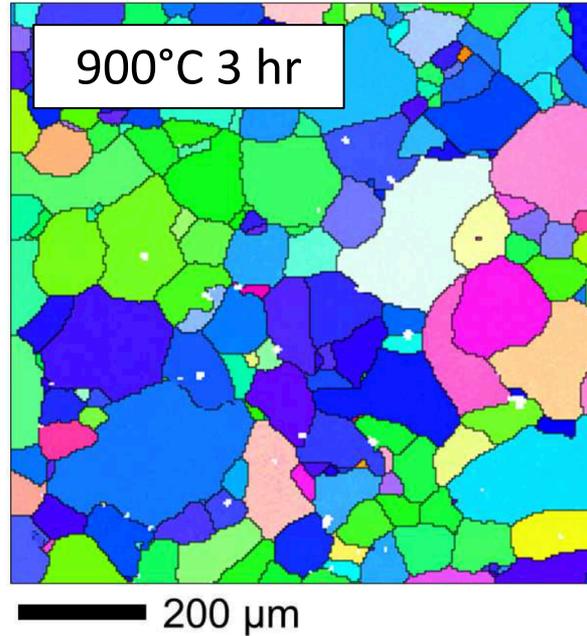
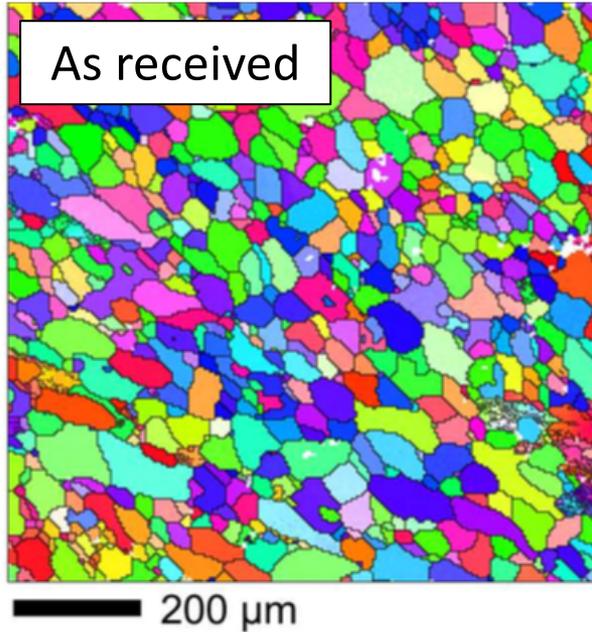
- R/Q per cell – 400 MHz: 85Ω ; 800 MHz: 84Ω
- G – 400 MHz, 800 MHz: 280Ω
- B_{pk}/E_{acc} – 400 MHz, 800 MHz: 4.1 mT/MV/m
- Static load – 5 W/m
- R_s – 400 MHz: $61.51 \cdot \exp(0.009411 \cdot B_{pk}) + 4 \text{ [n}\Omega\text{]}$
- [Private communication, S. Aull, CERN]

- COP^{-1} – 2 K: 808 W/W ; 4.4 K: 224 W/W
- [W. J. Schneider, et al. Gradient optimization for SC CW accelerators. *PAC 2003*, pp. 2863–2865, 2003.]

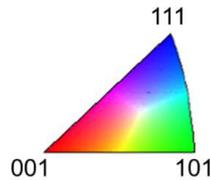
Cavity Prep	N-doped bulk Nb	120 C baked bulk Nb	Nb/Cu	Nb ₃ Sn
Level of Technical Maturity	Production (LCLS-II or XFEL) / R&D (1- and 5-cell cavities) / 800 MHz interpolation		Production (LHC) / R&D (flat plates)	R&D (1-cell) / goal
F [MHz]	1300 / 650 / 800		400	1300 / 800
T [K]	2	2	4.5	4.5
R _{BCS} @ field [nΩ @ MV/m]	4.5 @ 16 / 2 @ 16 / 3 @ 16	11 @ 20 / 3 @ 20 / 4.5 @ 20		7 @ 16 / 3 @ 16
Primary R _{res} source	Flux: 1.5 / 0.8 / 1.1 nΩ/mG	Flux: 0.5 / 0.3 / 0.4 nΩ/mG	Under study, also Q-slope	Under study, also flux
R _{res} [nΩ]	2 + 3 mG trapped: 6.5 / 4.4 / 5.3	6 + 3 mG trapped: 7.5 / 6.9 / 7.2		10 / 10
Approximate R _{tot} [nΩ]	16 MV/m: 11 / 6.4 / 8.3	20 MV/m: 18.5 / 9.4 / 11.6	10 MV/m: 320 / 104	15 MV/m: 17 / 13
Reference	M. Martinello [to be published]		S. Aull, SRF 2015	S. Posen and D. Hall, SUST 2017; D. Hall TTC 2017

Backup

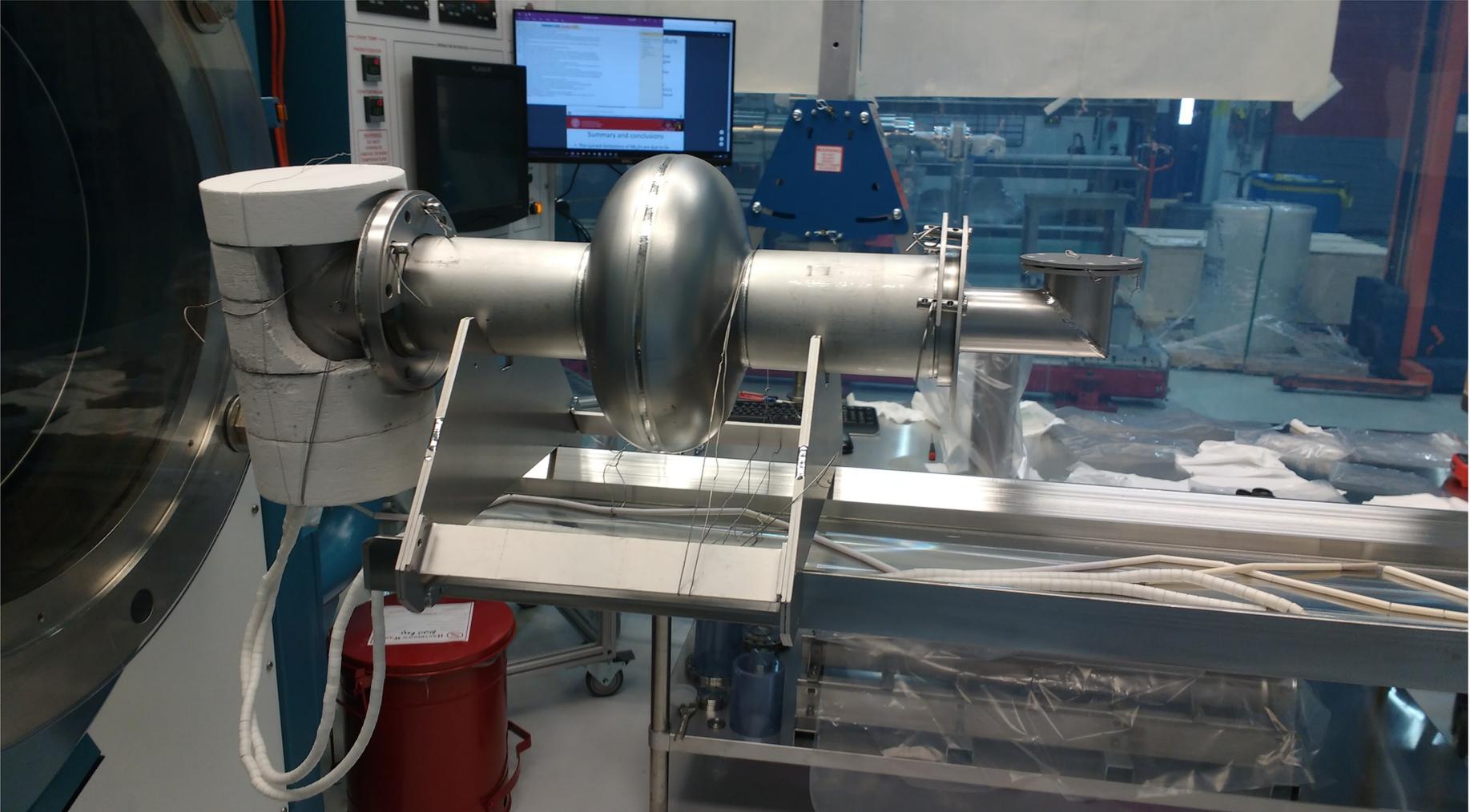
Flux Expulsion and High Temperature Treatment



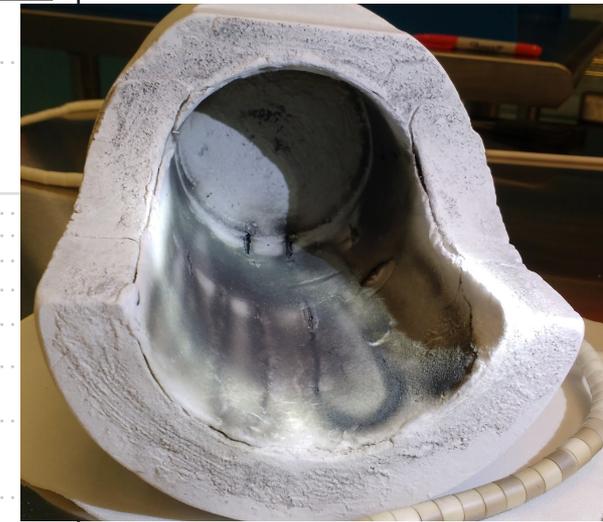
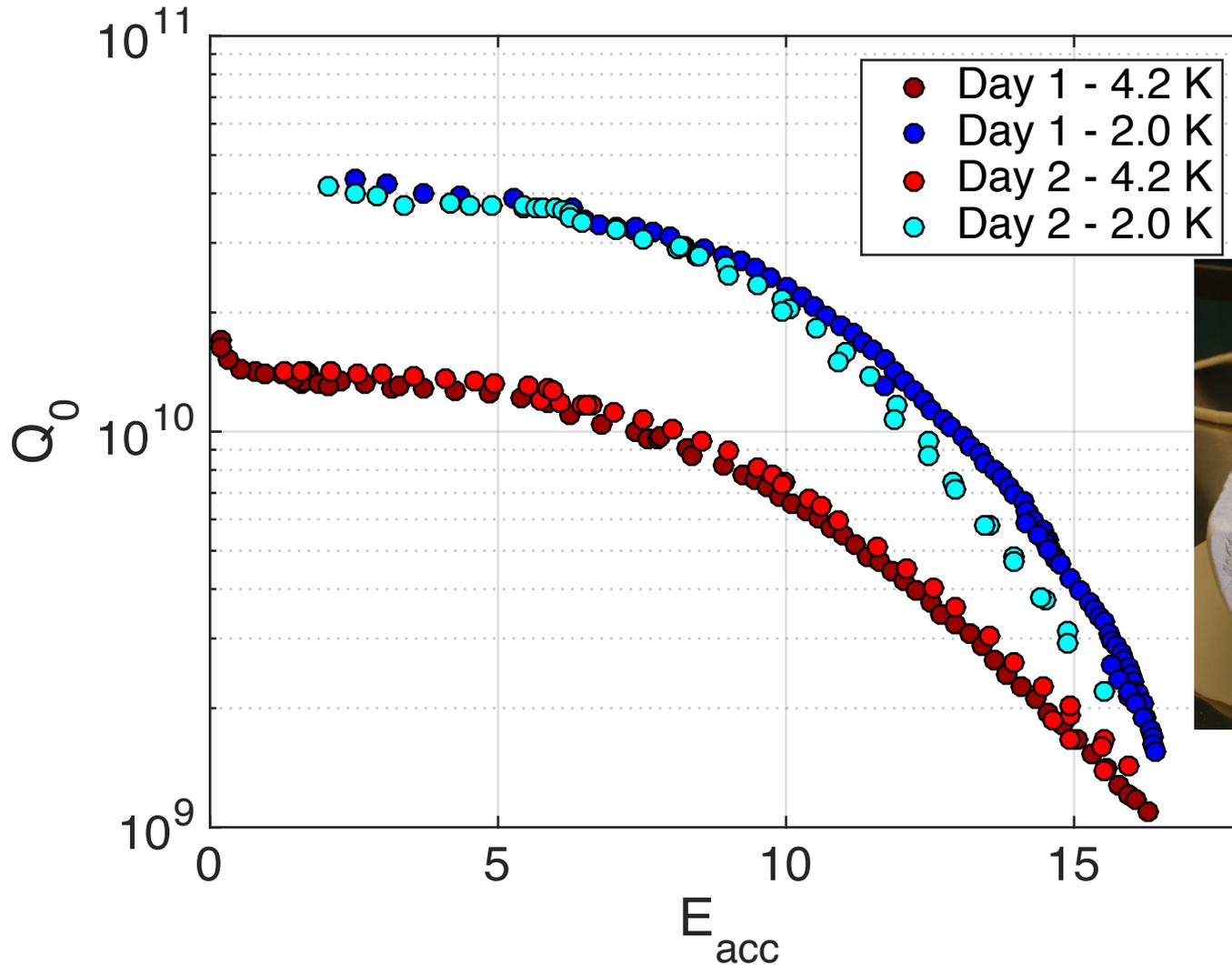
- Experiments suggest trapping is linked to dislocations (e.g. grain boundaries)
- High temperature treatment reduces pinning



First Fermilab Nb₃Sn Cavity Coated



First Fermilab Nb₃Sn Cavity Coated



- D. Gonnella IPAC17

